

VS-16TTS...FPPbF Series, VS-16TTS...FP-M3 Series

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Vishay Semiconductors

High Voltage Phase Control Thyristor, 16 A



ı	U-220A	B F	ULL	PA	n

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PRODUCT SUMMARY				
Package	TO-220AB FP			
Diode variation	Single SCR			
I _{T(AV)}	10 A			
V_{DRM}/V_{RRM}	800 V, 1200 V			
V_{TM}	1.4 V			
I _{GT}	60 mA			
T_J	- 40 °C to 125 °C			

FEATURES

- · Designed and qualified for industrial level
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 approved
- 125 °C max. operating junction temperature
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А				

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10	Δ.			
I _{RMS}		16	A			
V _{DRM} /V _{RRM}		800/1200	V			
I _{TSM}		200	Α			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/μs			
TJ	Range	- 40 to 125	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-16TTS08FPPbF, VS-16TTS08FP-M3	800	800	10			
VS-16TTS12FPPbF, VS-16TTS12FP-M3	1200	1200	10			



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	
PANAMETEN	STWIDOL				MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 70 °C,	180° conduction, half sine wave	1	0	
Maximum RMS on-state current	I _{RMS}			1	6	Α
Maximum peak, one-cycle,	1	10 ms sine p	oulse, rated V _{RRM} applied	1	70	_ A
non-repetitive surge current	I _{TSM}	10 ms sine p	oulse, no voltage reapplied	2	00	1
Marriage and 124 four fracing a	I ² t	10 ms sine pulse, rated V _{RRM} applied		1-	44	A ² s
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A-S
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		000	A²√s
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1	.4	٧
On-state slope resistance	r _t	T 105 °C		24	4.0	mΩ
Threshold voltage	V _{T(TO)}	$T_{\rm J} = 125 ^{\circ}{\rm C}$		1	.1	V
Maximum various and divast lackage current	1 /1	T _J = 25 °C	V Peted V A/	0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_{\rm J} = 125 ^{\circ}{\rm C}$ $V_{\rm R} = {\rm Rated} V_{\rm RRM}/V_{\rm DRM}$		1	0	
Holding current	l _H	Anode supply = 6 V, resistive load, initial I _T = 1 A 16TTS08FP, 16TTS12FP, T _J = 25 °C		-	150	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		2	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \max$	linear to 80 %, V _{DRM} = R _g - k = Open	5	00	V/µs
Maximum rate of rise of turned-on current	dI/dt			1	50	A/µs

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P_{GM}		8.0	w		
Maximum average gate power	P _{G(AV)}		2.0	7 **		
Maximum peak positive gate current	+ I _{GM}		1.5	Α		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	l _{GT}	Anode supply = 6 V, resistive load, T _J = - 10 °C	90			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	60	mA		
		Anode supply = 6 V, resistive load, T _J = 125 °C	35			
		Anode supply = 6 V, resistive load, T _J = - 10 °C	3.0			
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	v		
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	7 °		
Maximum DC gate voltage not to trigger V _{GD}		T 105 00 W But d at	0.25			
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA		

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T _J = 125 °C	4	μs			
Typical turn-off time	tq	1) = 125 0	110				

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque -	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf ⋅ in)
Madiandada			Coop et de TO 200AB FULL BAK (04A/0)	16TTS	08FP
Marking device			Case style TO-220AB FULL-PAK (94/V0)	16TTS12FP	

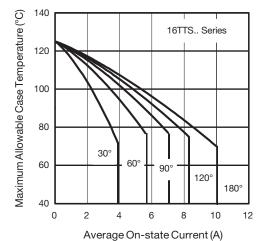


Fig. 1 - Current Rating Characteristics

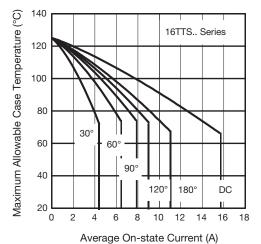


Fig. 2 - Current Rating Characteristics

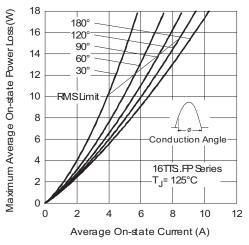


Fig. 3 - On-State Power Loss Characteristics

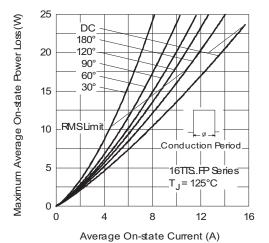


Fig. 4 - On-State Power Loss Characteristics

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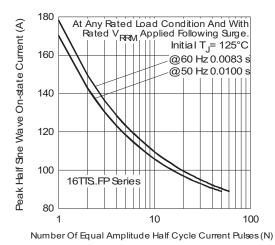


Fig. 5 - Maximum Non-Repetitive Surge Current

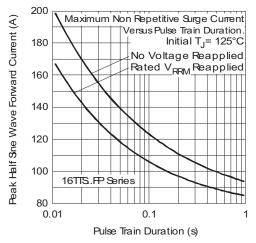


Fig. 6 - Maximum Non-Repetitive Surge Current



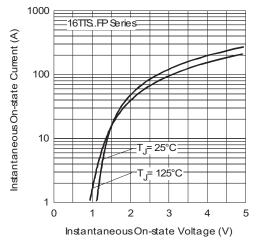


Fig. 7 - On-State Voltage Drop Characteristics

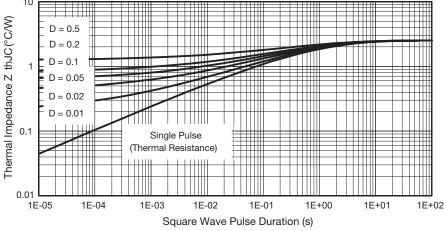
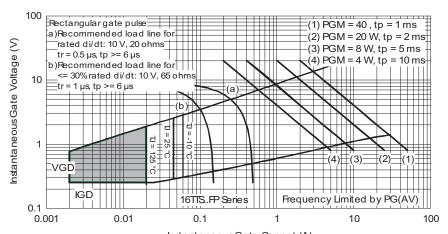


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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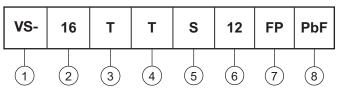
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Instantaneous Gate Current (A)
Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

7 - FULL-PAK

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

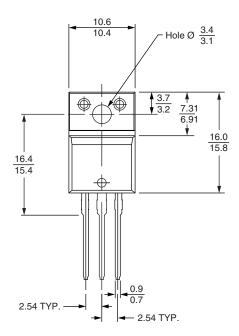
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-16TTS08FPPbF	50	1000	Antistatic plastic tubes				
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes				
VS-16TTS12FPPbF	50	1000	Antistatic plastic tubes				
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes				

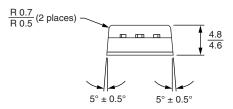
LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95072				
Dort marking information	TO-220FP PbF	www.vishay.com/doc?95069				
Part marking information	TO-220FP -M3	www.vishay.com/doc?95456				

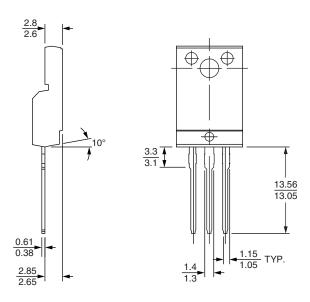


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DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



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